

RGB Video Amplifier System for Monitors

Description

The U2203B-A is a wideband video amplifier IC system especially designed for use in high-resolution RGB monitors. The IC includes three well matched video amplifiers, three gated differential amplifiers for black-

level clamping and brightness control and the function for simultaneously contrast control. Separate adjustment of the maximum gain of each channel is also possible.

Features

- 3 channels, high bandwidth (90 MHz @ −3 dB)
- Matched attenuators for contrast control
- Black-level clamping for brightness control
- Independent gain control of each amplifier
- ESD protection according to MIL-STD. 883

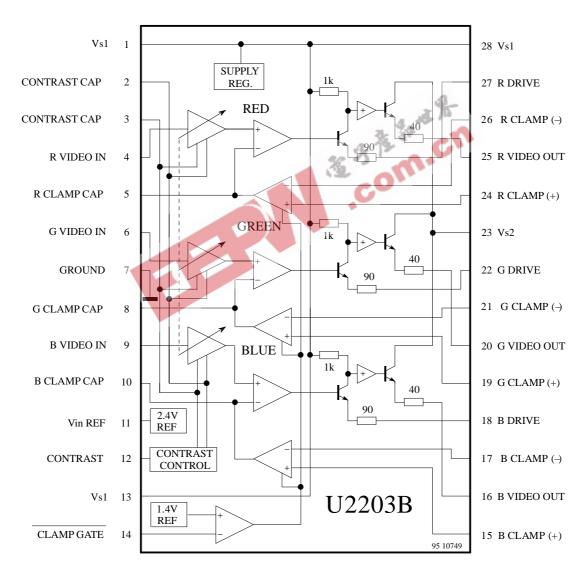
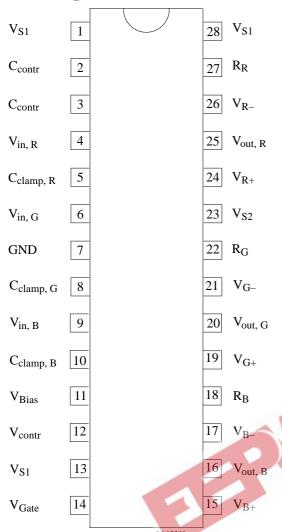


Figure 1. Block diagram



Pin Description



Pin	Symbol	Function
1	V_{S1}	Supply voltage
2	C _{contr}	Contrast cap.
3	C _{contr}	Contrast cap.
4	V _{in, R}	Video input (R)
5	C _{clamp, R}	Clamp cap. (R)
6	V _{in, G}	Video input (G)
7	GND	Ground
8	C _{clamp, G}	Clamp cap. (G)
9	V _{in, G}	Video input (B)
10	C _{clamp, B}	Clamp cap. (B)
11	V_{Bias}	Bias voltage (RGB-inputs)
12	V _{contr}	Contrast control
13	V_{S1}	Supply voltage
14	V_{Gate}	Inverted clamp gate
15	V_{B+}	Clamp amplifier (B+)
16	V _{in, B}	Video output (B)
17	V_{B-}	Clamp amplifier (B-)
18	R_{B}	Drive resistor (B)
19	V_{G^+}	Clamp amplifier (G+)
20	V _{out, G}	Video output (G)
21	V_{G-}	Clamp amplifier (G–)
22	R_{G}	Drive resistor (G)
23	V_{S2}	Supply voltage (outputs)
24	V_{R+}	Clamp amplifier (R+)
25	V _{out, R}	Video output (R)
26	V_{R-}	Clamp amplifier (R–)
27	R_R	Drive resistor (R)
28	V_{S1}	Supply voltage

Figure 2. Pinning

Absolute Maximum Ratings

Para	ameters	Symbol	Value	Unit
Supply voltage Pins 1, 13, 28 and 23		V_{S}	13.5	V
Input voltage at all other pir	ıs	V _{in}	0 toV_{S}	V
Video output current Pins 16, 20 and 25		I_{V}	28	mA
Junction temperature		Ti	125	°C
Storage temperature range		$T_{\rm stg}$	-40 to 125	°C

Operating Range

Paran	neters	Symbol	Value	Unit
Ambient temperature range		T _{amb}	0 to 80	°C
Supply voltage range	Pins 1, 13, 23 and 28	V_{S2}, V_{S1}	11.0 to 13.0	V



Thermal Resistance

Parameters		Symbol	Value	Unit
Junction ambient	(DIP28)	R_{thJA}	46	K/W

Electrical Characteristics

Test conditions unless otherwise specified, reference point Pin 7, $T_{amb} = 25^{\circ}C$, $V_{S1} = V_{S2} = 12 \text{ V}$, $V_{12} = 6 \text{ V}$ (contrast); $V_{14} = 0 \text{ V}$ (inv. gating); $V_{15} = V_{19} = V_{24} = 2 \text{ V}$ (brightness)

Parameters	Test Conditions / Pins	Symbol	Min.	Тур.	Max.	Unit	
DC-values							
Supply current	V _{S1} only,	I_{S1}		60	70	mA	
	Pins 1, 13 and 28						
Input bias voltage	Pin 11	VinREF	2.3		2.5	V	
Input bias current	Pins 4, 6 and 9	I _{inREF}	1	5	10	μΑ	
Switching voltage gating "on"	Pin 14	VG "L"	0.8	1.3		V	
Switching voltage gating "off"	Pin 14	VG "H"		1.5	2.0	V	
Switching current gating "on"	$V_{14} = 0.8 \text{ V}$ Pin 14	IG "L"	-1 g	-0.01		μΑ	
Switching current gating "off"	$V_{14} = 2.0 \text{ V}$ Pin 14	IG "H"	30	5	8	μΑ	
Charge current clamping capacitor	$V_{5,8,10} = 0 \text{ V}$ Pins 5, 8 and 10	ICL+	0.8	1.0	1.2	mA	
Discharge current clamping capacitor	$V_{5,8,10} = 5 \text{ V}$ Pins 5, 8 and 10	ICL-	-1.2	-1.0	-0.8	mA	
Video outputs, V _O	Pins 16, 20 and 25		•		'	•	
Low level	$V_{5,8,10} = 0 \text{ V}$	V _{O"L"}		0.8	1.0	V	
High level	$V_{5,8,10} = V_S$	Vo"H"	8.0	8.6		V	
Output offset between two amplifiers	V_{15} , V_{19} , $V_{24} = 2 V$	ΔV_{O} (2 V)			±50	mV	
	$V_{15}, V_{19}, V_{24} = 4 V$	ΔV _O (4 V)			±50	mV	
Video gain $V_{15} = V_{19} = V_{24} = 4 \text{ V (brightness)}; f_{IN} = 1 \text{ MHz}$							
Maximum video gain	$V_{12} = 12 \text{ V}$	G _{Vmax}	16.0	17.7		dB	
Middle video gain	$V_{12} = 5 V$	GV _{mid}		8.5		dB	
Dynamic gain range		GVD		50		dB	
Video gain match	$V_{12} = 12 \text{ V}$	GVM _{max}		±0.1		dB	
(any 2 outputs)	$V_{12} = 5 V$	GVM _{mid}		±0.1		dB	
	$V_{12} = 2.2 V$ 1)	GVM ₋₃₀		±0.3		dB	
Video bandwidth							
unpeaked ($C = 0 pF$)	$V_{12} = 12 \text{ V } (f_{-3dB})$	BWV		65		MHz	
optimal peaking (C = 27 pF)	$V_{12} = 12 \text{ V } (f_{-3dB})$	BWV_P		90		MHz	
Video cross talk	$\begin{aligned} f_{IN} &= 10 \text{ kHz} \\ f_{IN} &= 10 \text{ MHz} \end{aligned}$	CT _{10kHz} CT _{10MHz}	-50	-47		dB dB	

¹⁾ Measured 30 dB below maximum gain

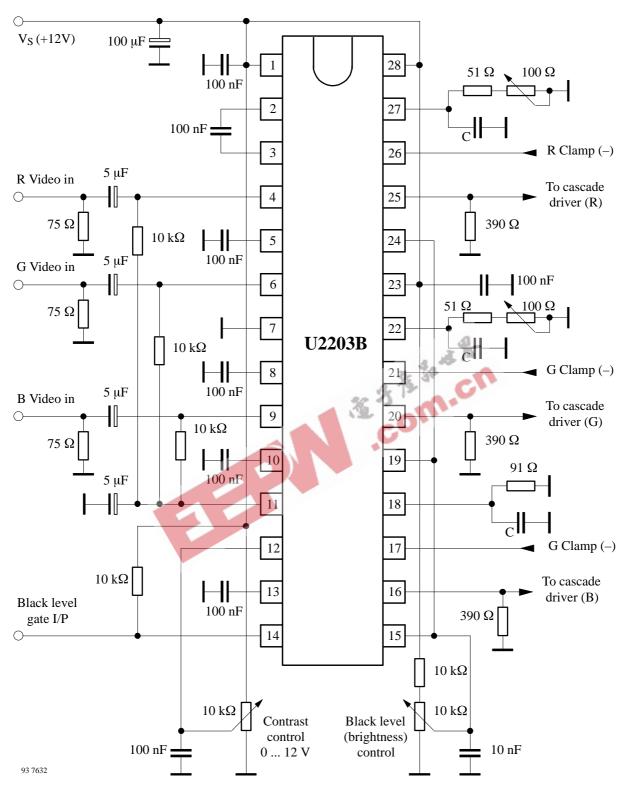


Figure 3. Typical application circuit

AC Characteristics

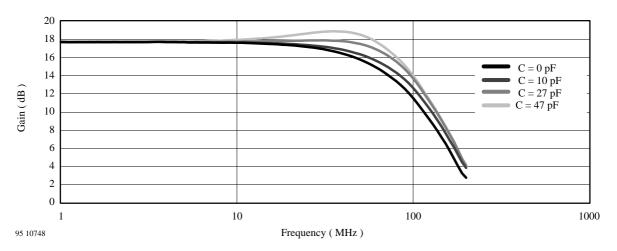


Figure 4. Gain vs. frequency (various peaking), $V_{12} = 12 \text{ V}$ (contrast), $V_{15} = V_{19} = V_{24} = 4 \text{ V}$ (brightness)

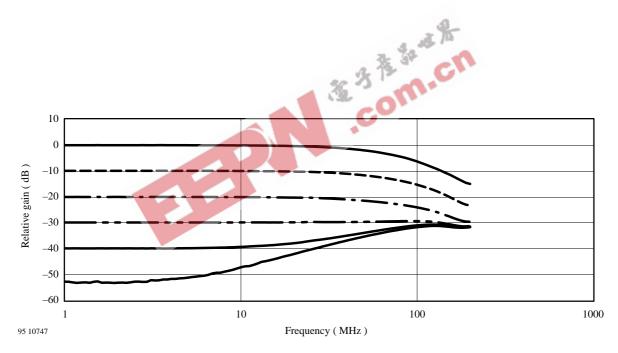


Figure 5. Relative gain vs. frequency (no peaking), V_{12} = variable (contrast), V_{15} = V_{19} = V_{24} = 4 V (brightness), 0 dBrel = 17.7 dB, C = 0 pF



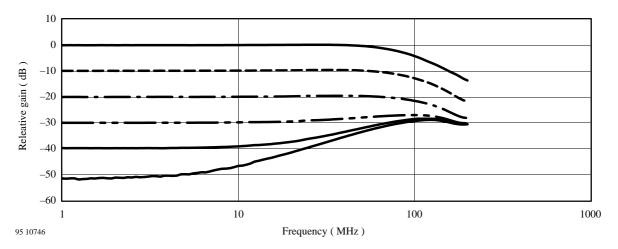
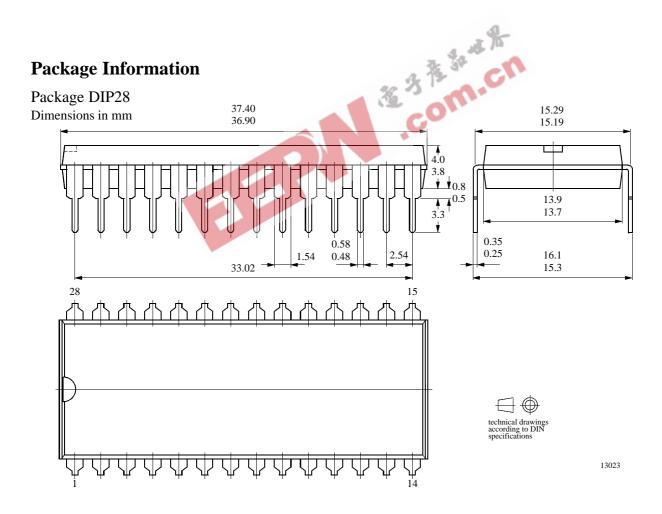


Figure 6. Rel. gain vs. frequency (optimized peaking), V_{12} = variable (contrast), V_{15} = V_{19} = V_{24} = 4 V (brightness), 0 dBrel = 17.7 dB, C = 27 pF





Ozone Depleting Substances Policy Statement

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- Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

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- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

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